

**Amendments to the Specification**

Please replace the paragraph beginning on page 25, line 20, with the following rewritten paragraph:

In the present embodiment, since a wetting layer, for example a Ti film, can hold gaseous components (oxygen, hydrogen, water vapor, and nitrogen) dissolved therein, to as much as several atomic percentages, removing the gaseous components from the interlayer dielectric I2 prior to the formation of the wetting layer is extremely effective for forming a good aluminum layer within a via-hole. If the gaseous components in the interlayer dielectric I2 underneath the wetting layer are not removed sufficiently, the gaseous components within the interlayer dielectric I2 will be released during the formation of the wetting layer, and these gases will be taken up into the wetting layer. In addition, these gases will be desorbed from the wetting layer and will exit from the interface with the aluminum layer during the formation of the aluminum layer, which will adversely affect the adhesiveness and fluidity of the aluminum layer. ~~The wetting layer may also include zirconium.~~

Please replace the Abstract with the attached amended Abstract.